

Author: Kunihiro Suzuki Fujitsu limited Japan



eISBN: 978-1-60805-792-4

Ion Implantation and Activation volume 3

www.benthamscience.com/ebooks/9781608057924

About the ebook

This e-book series presents the derivation process of related models in a comprehensive step by step manner. This volume describes the diffusion phenomenon under the thermal equilibrium on point defect concentration and the features of transient enhanced diffusion (TED). The volume also presents methods for the oxidation and redistribution of impurities in polycrystalline silicon for extraction as well as some analytical models related to the VLSI process

Contents

- Diffusion Under Thermal Equilibrium
- Paring Diffusion Equation
- Experimental Data Associated with Transient Diffusion
- Simple Treatment of Transient Enhanced Diffusion
- Thermal Oxidation
- Segregation
- Analytical Diffusion Profiles Under Various Boundary Conditions

For more information on how to order the electronic or print version of the book, contact subscriptions@benthamscience.org

